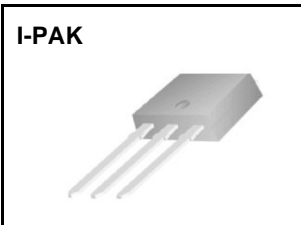
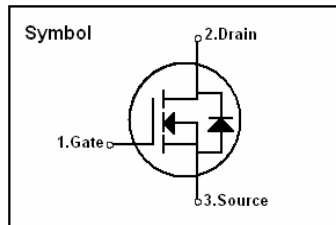


N-Channel MOSFET

Features

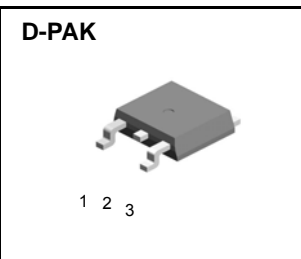
- 3.0A, 600V, $R_{DS(on)}=4.0\ \Omega$ @ $V_{GS}=10V$
- Gate charge (Typical 7.0nC)
- High ruggedness
- Fast switching
- 100% Avalanche Tested
- Improved dv/dt capability



General Description

This N-channel enhancement mode field-effect power transistor using HG semiconductor's advanced planar stripe, DMOS technology intended for off-line switch mode power supply.

Also, especially designed to minimize $r_{ds(on)}$ and high rugged avalanche characteristics. The D-PAK pkg is well suited for charger SMPS and small power inverter application.



Absolute Maximum Ratings

Symbol	Parameter	Value	Units
V_{DSS}	Drain to Source Voltage	600	V
I_D	Continuous Drain Current (@ $T_C = 25^\circ\text{C}$)	3.0	A
	Continuous Drain Current (@ $T_C = 100^\circ\text{C}$)	1.9	A
I_{DM}	Drain Current Pulsed (Note 1)	12	A
V_{GS}	Gate to Source Voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	148	mJ
E_{AR}	Repetitive Avalanche Energy (Note 1)	4.5	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5	V/ns
P_D	Total Power Dissipation (@ $T_C = 25^\circ\text{C}$)	45	W
	Derating Factor above 25°C	0.36	W/ $^\circ\text{C}$
T_{STG}, T_J	Operating Junction Temperature & Storage Temperature	- 55 ~ 150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for soldering purpose, 1/8 from Case for 5 seconds.	300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Value			Units
		Min.	Typ.	Max.	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	-	-	2.78	$^\circ\text{C}/\text{W}$
$R_{\theta CS}$	Thermal Resistance, Case to Sink	-	-	50	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	-	-	110	$^\circ\text{C}/\text{W}$

Electrical Characteristics ($T_C = 25\text{ }^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	600	-	-	V
BV_{DSS}/T_J	Breakdown Voltage Temperature coefficient	$I_D = 250\mu A$, referenced to $25\text{ }^\circ\text{C}$	-	0.4	-	$V/^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS} = 600V, V_{GS} = 0V$	-	-	10	μA
		$V_{DS} = 480V, T_C = 125\text{ }^\circ\text{C}$	-	-	100	μA
I_{GSS}	Gate-Source Leakage, Forward	$V_{GS} = 30V, V_{DS} = 0V$	-	-	100	nA
	Gate-source Leakage, Reverse	$V_{GS} = -30V, V_{DS} = 0V$	-	-	-100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.0	-	4.0	V
$R_{DS(on)}$	Static Drain-Source On-state Resistance	$V_{GS} = 10V, I_D = 1.0A$	-	-	4.0 (Note4)	Ω
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{GS} = 0V, V_{DS} = 25V, f = 1MHz$	-	570	720	pF
C_{oss}	Output Capacitance		-	150	215	
C_{rss}	Reverse Transfer Capacitance		-	310	450	
Dynamic Characteristics						
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 300V, I_D = 2.0A, R_G = 25$ see fig. 13. (Note 4, 5)	-	15	35	ns
t_r	Rise Time		-	75	140	
$t_{d(off)}$	Turn-off Delay Time		-	30	60	
t_f	Fall Time		-	35	60	
Q_g	Total Gate Charge	$V_{DS} = 480V, V_{GS} = 10V, I_D = 2.0A$ see fig. 12. (Note 4, 5)	-	15	20	nC
Q_{gs}	Gate-Source Charge		-	1.6	-	
Q_{gd}	Gate-Drain Charge(Miller Charge)		-	6	-	

Source-Drain Diode Ratings and Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit.
I_S	Continuous Source Current	Integral Reverse p-n Junction Diode in the MOSFET	-	-	2.0	A
I_{SM}	Pulsed Source Current		-	-	8.0	
V_{SD}	Diode Forward Voltage	$I_S = 1.5A, V_{GS} = 0V$	-	-	1.5	V
t_{rr}	Reverse Recovery Time	$I_S = 2.0A, V_{GS} = 0V, di/dt = 100A/\mu s$	-	600	-	ns
Q_{rr}	Reverse Recovery Charge		-	1.1	-	μC

*** NOTES**

1. Repeativity rating : pulse width limited by junction temperature
2. $L = 14.2mH, I_{AS} = 10.3A, V_{DD} = 50V, R_G = 50\Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 10.3A, di/dt \leq 300A/\mu s, V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$
5. Essentially independent of operating temperature.

Fig 1. On-State Characteristics

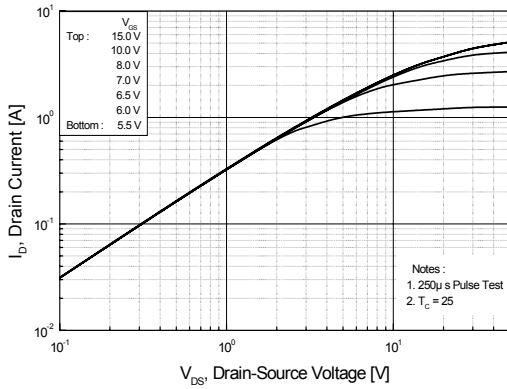


Fig 2. Transfer Characteristics

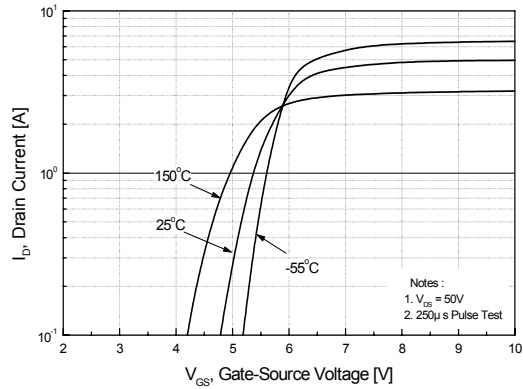


Fig 3. On Resistance Variation vs. Drain Current and Gate Voltage

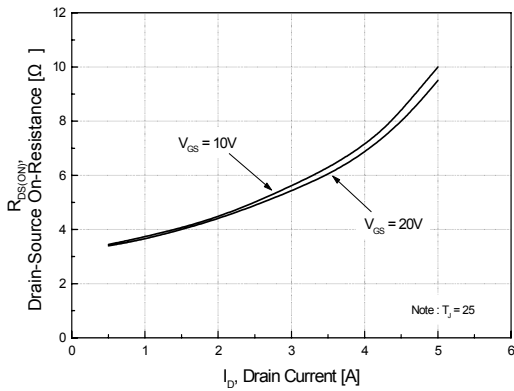


Fig 4. On State Current vs. Allowable Case Temperature

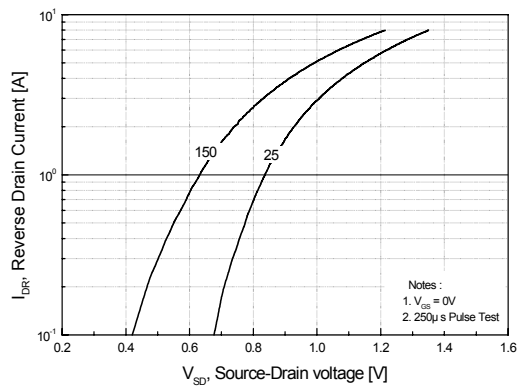


Fig 5. Capacitance Characteristics (Non-Repetitive)

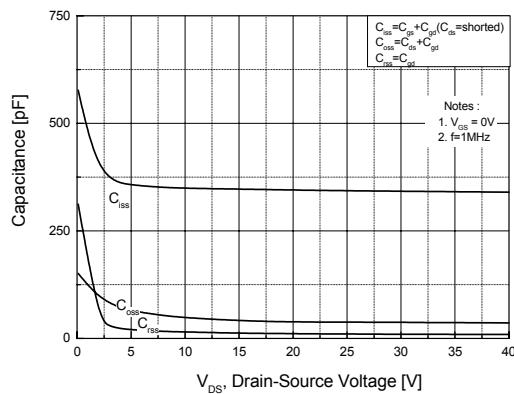


Fig 6. Gate Charge Characteristics

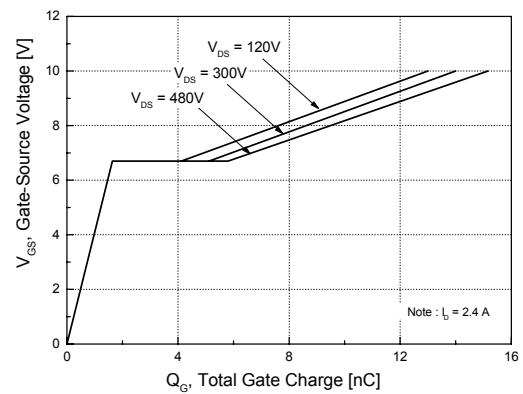


Fig 7. Breakdown Voltage Variation vs. Junction Temperature

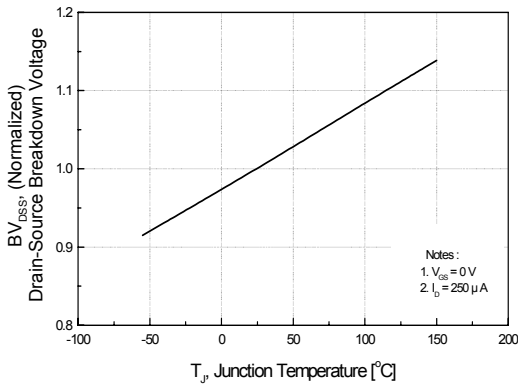


Fig 8. On-Resistance Variation vs. Junction Temperature

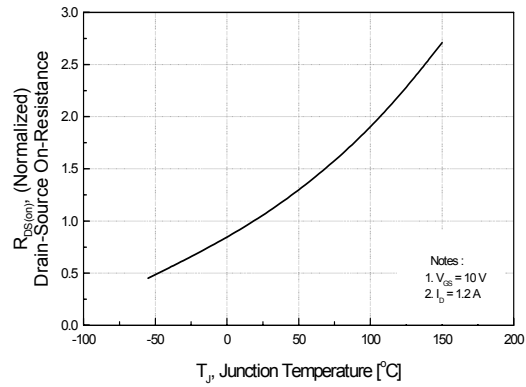


Fig 9. Maximum Safe Operating Area

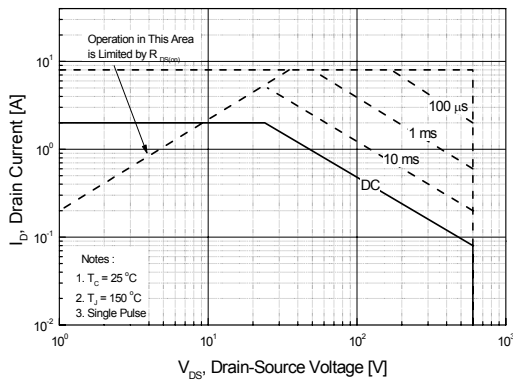


Fig 10. Maximum Drain Current

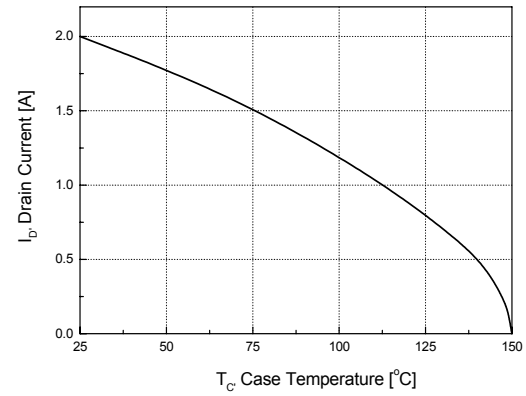


Fig 11. Transient Thermal Response Curve

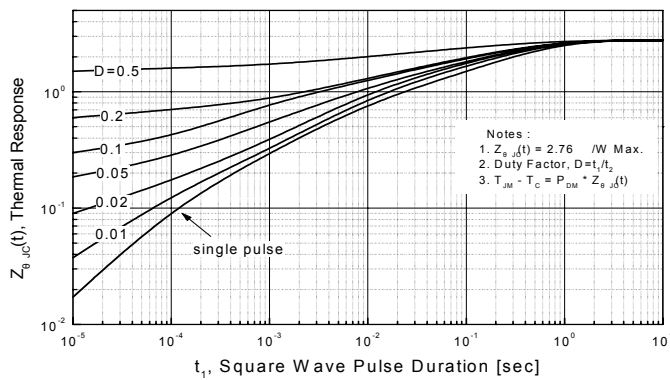


Fig. 12. Gate Charge Test Circuit & Waveforms

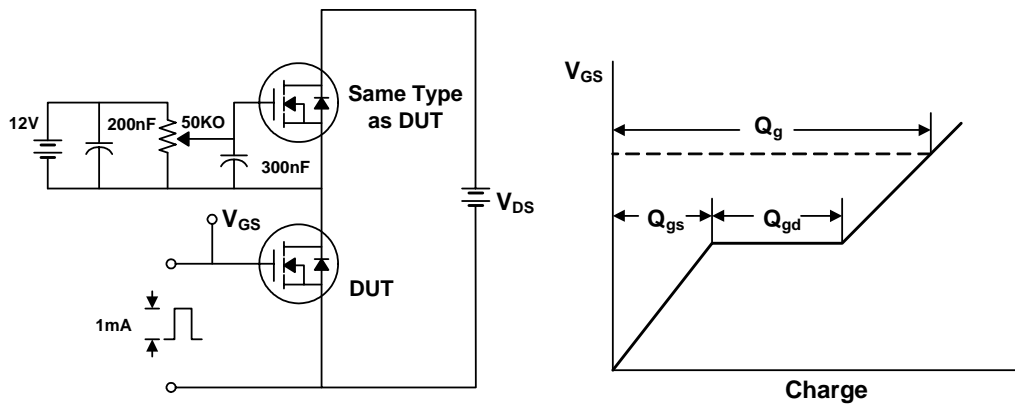


Fig 13. Switching Time Test Circuit & Waveforms

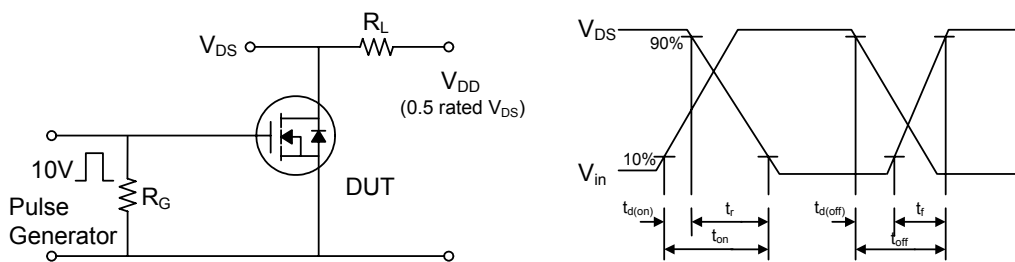


Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms

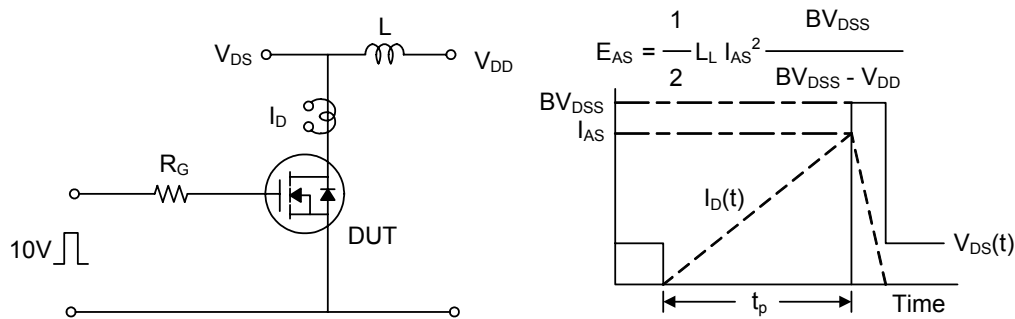


Fig. 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

